

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning on page 22, line 3, as follows:

With reference to FIG. 4A, the semiconductor switch according to the present embodiment comprises the two anode electrodes 7, and the cathode electrode 8 which are enclosed by an active layer 3. From two anode electrodes 7, one together with the cathode electrode 8 forms a Schottky barrier diode. In detail, referring to FIG. 4B, an i-AlGaAs layer is formed on an i-GaAs layer. An i-InGaAs layer as a channel layer is formed on the i-AlGaAs layer. A n-AlGaAs layer is formed on the i-InGaAs layer. The anode electrodes 7 are formed on the n-AlGaAs layer apart from each other. The ~~each~~ cathode electrode 8 is formed on the n-AlGaAs layer through a n^+ -GaAs layers. The anode electrode 7 are made by aluminum, gold, molybdenum, titanium, or tungsten silicide. The ~~each~~ cathode electrode is made by an alloy including AuGe or nickel. In addition, the other anode electrode 7, likewise, together with the cathode electrode 8 may be considered to form a Schottky barrier diode, or may be considered to be an additional electrode established as an annex to the Schottky barrier diode. Anyway the two anode electrodes 7 are both connected with the earth, and are disposed in parallel to each other in a predetermined direction on the semiconductor substrate (in this example, in the right-left lateral direction on the paper surface). In addition, the cathode electrode 8 is disposed so as to be sandwiched between the two anode electrodes 7 as well as, likewise, to be in parallel to each other in a predetermined direction on the semiconductor substrate. The anode electrodes 7 have undergone Schottky junction with semiconductor crystal, and the cathode electrode 8 has undergone ohmic junction with semiconductor crystal. Both the ends of the cathode electrode 8 in the predetermined direction operate respectively as the first input-output unit and the second input-output unit, and are respectively connected with the first input-output terminal 1 and the second input-output terminal 2. Such semiconductor switches are driven by supplying the cathode electrode 8 with negative voltage as well as zero bias outside the active layer 3 by a not-shown bias line via a resistance. At this time, when required, capacitance C1, C2, and C3 for DC cutting is inserted between the cathode electrode 8 and each input-output terminal.